ShiLing® 浙江世菱半导体有限公司
ZHEJIANG SHILING SEMICONDUCTOR CO.,LTD.

产品规格书

Specifcation of products

产品名称:整流管模块

产品型号:MDC200A-M2

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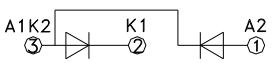
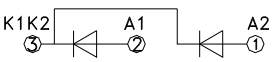
SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T_j (℃)	VALUE			UNIT
				Min	Type	Max	
$I_{T(AV)}$ $I_{F(AV)}$	Mean on-state current	180° half sine wave 50Hz Single side cooled,T_C=85°C	125		200		A
$I_{T(RMS)}$	RMS on-state current	Single side cooled,T_C=85°C	125		314		A
V_{DRM} V_{RRM}	Repetitive peak o ff-state voltage Repetitive peak reverse voltage	V_{DRM}&V_{RRM} tp=10ms V_{DSM}&V_{RSM}= V_{DRM}&V_{RRM}+200V respectively	125	600		1800	V
I_{DRM} I_{RRM}	Repetitive peak current	at V_{DRM} at V_{RRM}	125			9	mA
I_{TSM}	Surge on-state current	10ms half sine wave V_R=60%V_{RRM}	125			6. 80	KA
I^2t	I^2T for fusing coordination					231.2	A^2s*10^3
V_{TO}	Threshold voltage		125			0. 84	V
r_T	On-state slop resistance					1. 13	mΩ
V_{FM}	Peak on-state voltage	I_{TM}=600A	125		1. 3		V
V_{GD}	Non-trigger gate voltage	At 67%V_{DRM}	125			1. 3	V
$R_{th(j-c)}$	Thermal resistance Junction to heatsink	At 180^0 sine' Single side cooled				0. 170	°C /W
V_{iso}	Isolation voltage	50Hz, RM. S, t=1min, I_{iso}: 1mA (MAX)		3000			V
F_m	Thermal connection torque(M6)				5. 0		N.m
	Mounting torque(M6)				5. 0		N.m
T_{stg}	Stored temperature			-40		140	°C
W_t	Weight				190		g
Outline							

OUTLINE DRAWING & CIRCUIT DIAGRAM

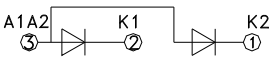
MDC



MDK



MDA



Rating and Characteristic

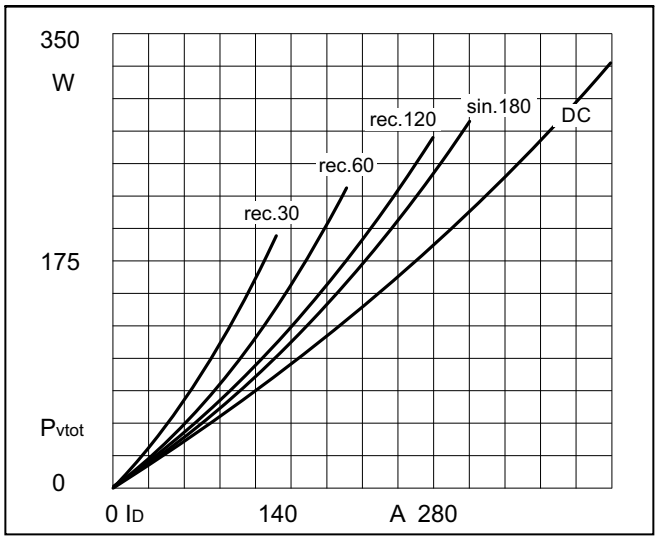


Fig1. Power dissipation

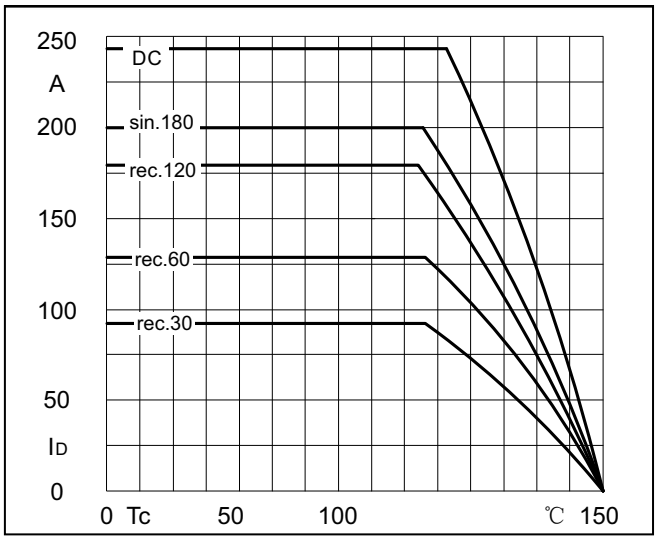


Fig2.Forward Current Derating Curve

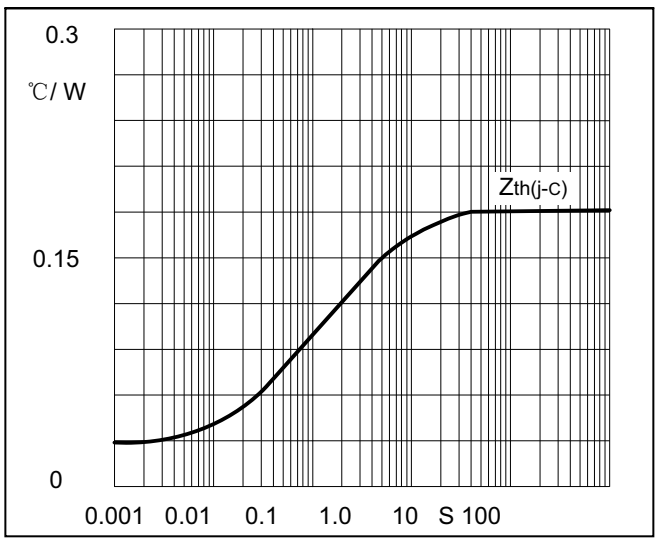


Fig3. Transient thermal impedance

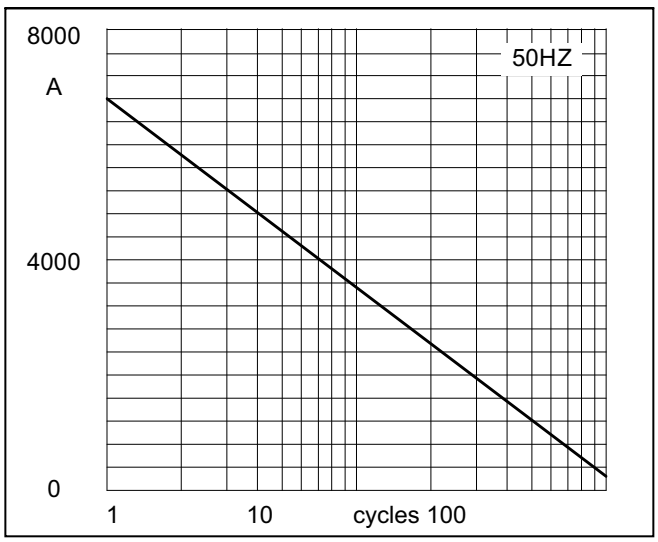


Fig4. Max Non-Repetitive Forward Surge Current

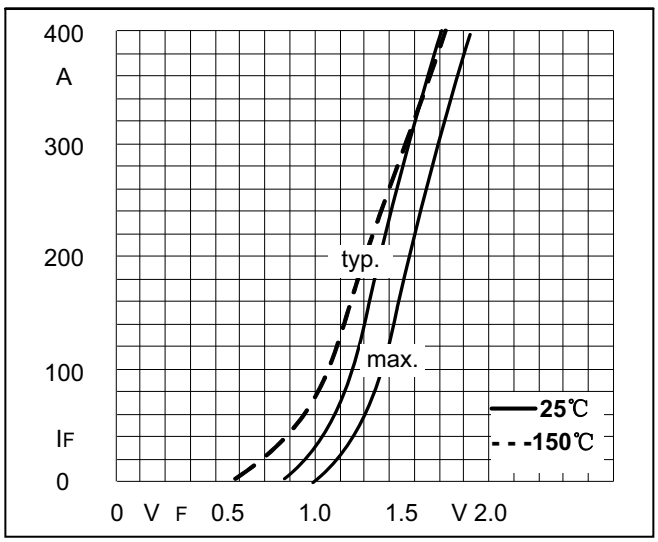


Fig5. Forward Characteristics

Outside Dimension